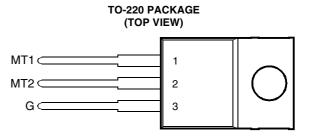
# BOURNS®

- High Current Triacs
- 12 A RMS
- Glass Passivated Wafer
- 400 V to 800 V Off-State Voltage
- Max I<sub>GT</sub> of 50 mA (Quadrants 1 3)



Pin 2 is in electrical contact with the mounting base.

#### absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING			VALUE	UNIT	
	TIC236D		400		
Repetitive peak off-state voltage (see Note 1)	TIC236M	N	600	v	
	TIC236S	V <sub>DRM</sub>	700		
	TIC236N		800		
Full-cycle RMS on-state current at (or below) 70°C case temperature (see Note 2)			12	A	
Peak on-state surge current full-sine-wave at (or below) 25°C case temperature (see Note 3)			100	A	
Peak gate current			±1	A	
Operating case temperature range			-40 to +110	°C	
Storage temperature range			-40 to +125	°C	
Lead temperature 1.6 mm from case for 10 seconds			230	°C	

NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.

 This value applies for 50-Hz full-sine-wave operation with resistive load. Above 70°C derate linearly to 110°C case temperature at the rate of 300 mA/°C.

3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of peak reverse volta ge and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.

#### electrical characteristics at 25°C case temperature (unless otherwise noted )

PARAMETER		TEST CONDITIONS			MIN	ТҮР	MAX	UNIT
I <sub>DRM</sub>	Repetitive peak off-state current	V <sub>D</sub> = Rated V <sub>DRM</sub>	$I_{G} = 0$	T <sub>C</sub> = 110°C			±2	mA
I <sub>GT</sub>		V <sub>supply</sub> = +12 V†	R <sub>L</sub> = 10 Ω	t <sub>p(g)</sub> > 20 μs		12	50	mA
	Gate trigger	$V_{supply} = +12 V^{\dagger}$	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs		-19	-50	
	current	V <sub>supply</sub> = -12 V†	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs		-16	-50	
		V <sub>supply</sub> = -12 V†	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs		34		
V <sub>GT</sub>		V <sub>supply</sub> = +12 V†	R <sub>L</sub> = 10 Ω	t <sub>p(g)</sub> > 20 μs		0.8	2	v
	Gate trigger	$V_{supply} = +12 V^{\dagger}$	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs		-0.8	-2	
	voltage	V <sub>supply</sub> = -12 V†	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs		-0.8	-2	
		$V_{supply} = -12 V^{\dagger}$	$R_L = 10 \Omega$	t <sub>p(g)</sub> > 20 μs		0.9	2	
V <sub>T</sub>	On-state voltage	I <sub>TM</sub> = ±17 A	l <sub>G</sub> = 50 mA	(see Note 4)		±1.4	±2.1	V

† All voltages are with respect to Main Terminal 1.

NOTE 4: This parameter must be measured using pulse techniques,  $t_p = \le 1$  ms, duty cycle  $\le 2$  %. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

# PRODUCT INFORMATION

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### electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

PARAMETER		TEST CONDITIONS			MIN	ТҮР	MAX	UNIT
I <sub>Н</sub>	Holding current	V <sub>supply</sub> = +12 V† V <sub>supply</sub> = -12 V†	l <sub>G</sub> = 0 l <sub>G</sub> = 0	Init' I <sub>TM</sub> = 100 mA Init' I <sub>TM</sub> = -100 mA		22 -12	40 -40	mA
IL.	Latching current	V <sub>supply</sub> = +12 V† V <sub>supply</sub> = -12 V†	(see Note 5)				80 -80	mA
dv/dt	Critical rate of rise of off-state voltage	V <sub>D</sub> = Rated V <sub>D</sub>	I <sub>G</sub> = 0	$T_{C} = 110^{\circ}C$		±400		V/µs
dv/dt <sub>(c)</sub>	Critical rise of commutation voltage	$V_D$ = Rated $V_D$ di/dt = 0.5 I <sub>T(RMS)</sub> /ms		T <sub>C</sub> = 80°C I <sub>T</sub> = 1.4 I <sub>T(RMS)</sub>	±1.2	±9		V/µs
di/dt	Critical rate of rise of on -state current	V <sub>D</sub> = Rated V <sub>D</sub> di <sub>G</sub> /dt = 50 mA/µs	I <sub>GT</sub> = 50 mA	$T_{C} = 110^{\circ}C$		±100		A/µs

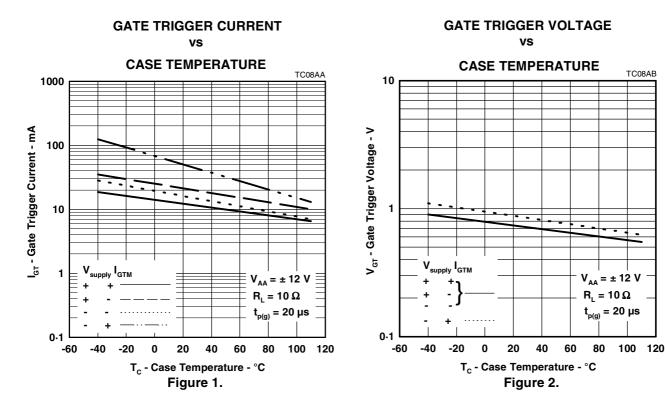
† All voltages are with respect to Main Terminal 1.

NOTE 5: The triacs are triggered by a 15-V (open-circuit amplitude) pulse supplied by a generator with the following characteristics:  $R_G = 100 \ \Omega$ ,  $t_{p(g)} = 20 \ \mu s$ ,  $t_r = \le 15 \ ns$ ,  $f = 1 \ kHz$ .

#### thermal characteristics

PARAMETER			TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			2	°C/W
R <sub>0JA</sub>	Junction to free air thermal resistance			62.5	°C/W

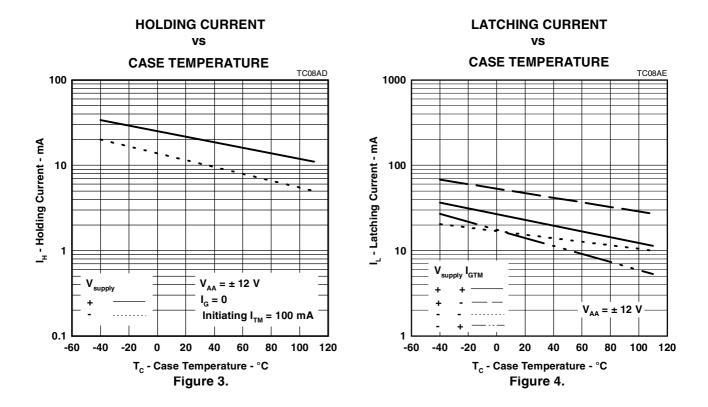
## **TYPICAL CHARACTERISTICS**



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# **TYPICAL CHARACTERISTICS**



#### PRODUCT INFORMATION

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